

N-Channel Enhancement Mode MOSFET

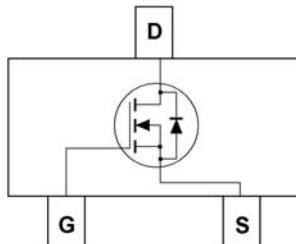
- Features

60V/0.5A,
 $R_{DS(ON)} = 4\Omega(\text{MAX})$ @ $V_{GS} = 10V$. $I_D = 0.5A$
 $R_{DS(ON)} = 7.5\Omega(\text{MAX})$ @ $V_{GS} = 4.5V$. $I_D = 0.2A$
 Super High dense cell design for extremely low $R_{DS(ON)}$.
 Reliable and Rugged.
 SOT-23 for Surface Mount Package

- General Description

Power Management in Desktop Computer or
 DC/DC Converters .

- Pin Configurations



SOT23

- Absolute Maximum Ratings @ $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	0.5	A

FS2N7002

- Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=10\mu\text{A}$	60	--	--	V
Zero-Gate Voltage Drain Current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	--	--	1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{\text{GS}}=20\text{V}, V_{\text{DS}}=0\text{V}$	--	--	100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{\text{GS}}=-20\text{V}, V_{\text{DS}}=0\text{V}$	--	--	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=250\mu\text{A}$	1	--	2.5	V
Static Drain-source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=0.5\text{A}$	--	3.25	4	Ω
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=0.2\text{A}$	--	5.5	7.5	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=0.2\text{A}$	--	--	2.5	V
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}$ $f=1\text{MHz}$		22	45	pF
Output Capacitance	C_{oss}			11	24	
Reverse Transfer Capacitance	C_{rss}			2	5	

- Typical Performance Characteristics

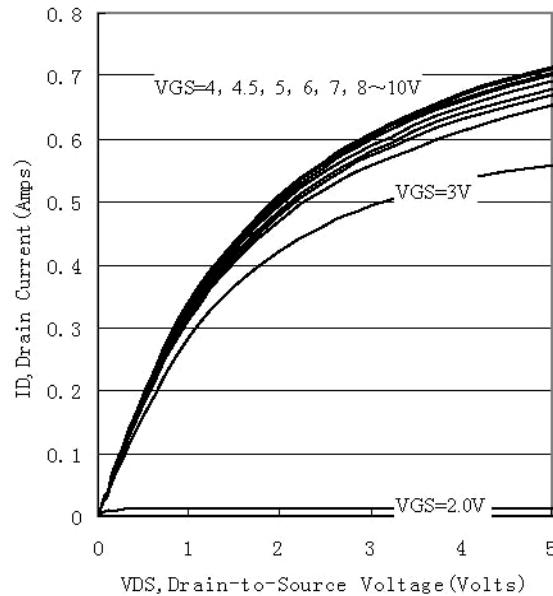


Figure 1. Output Characteristics

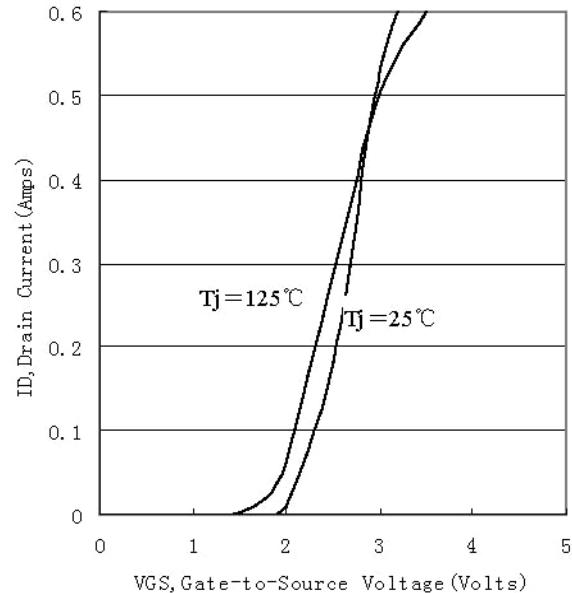


Figure 2. Transfer Characteristics

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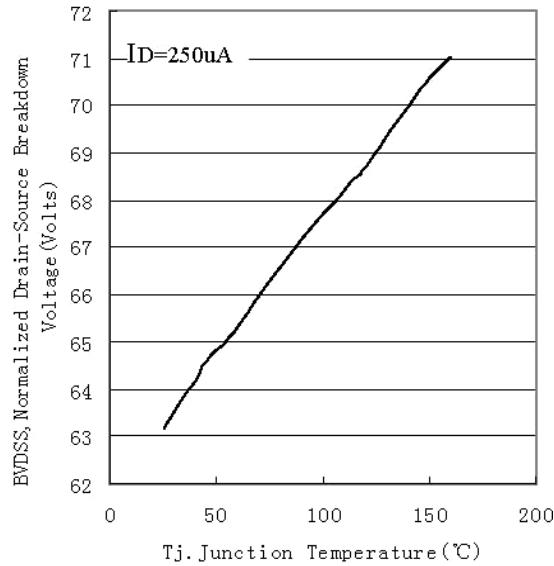


Figure 3. Breakdown Voltage Variation with Temperature

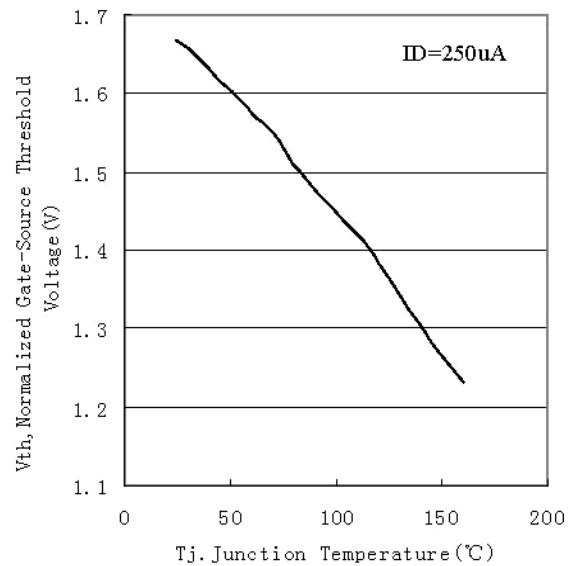


Figure 4. Gate Threshold Variation with Temperature

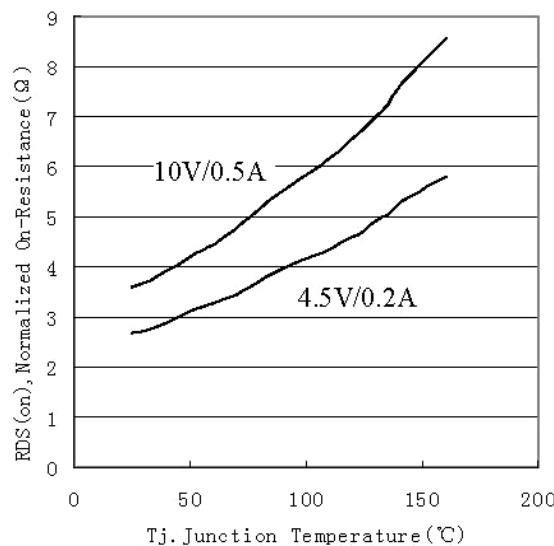


Figure 5. On-Resistance Variation with Temperature

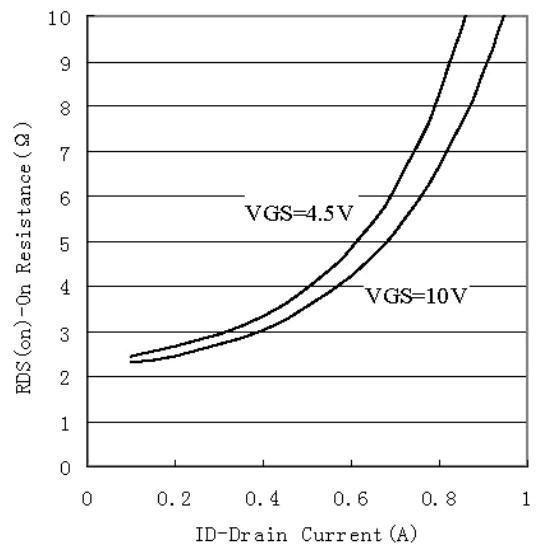


Figure 6. On-Resistance vs. Drain Current

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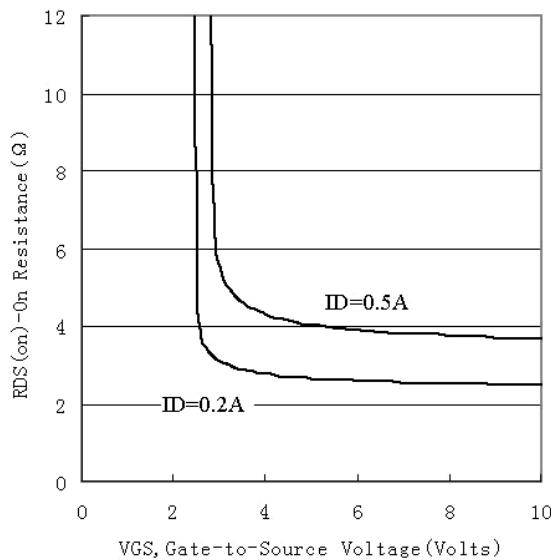


Figure 7. On-Resistance vs. Gate-to-Source Voltage

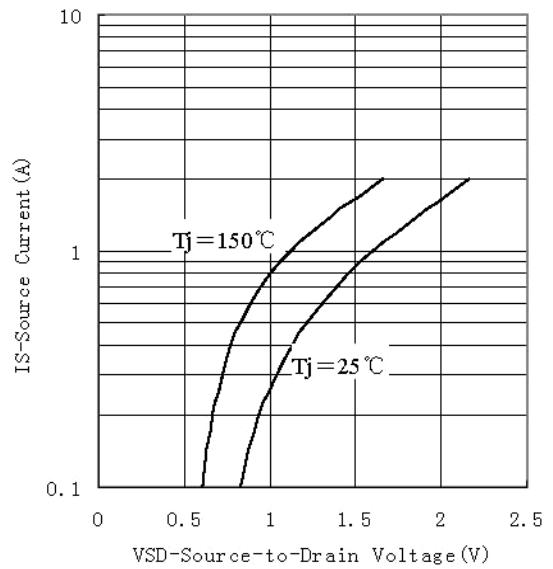


Figure 8. Source-Drain Diode Forward Voltage

- **Package Information**

